



BD139

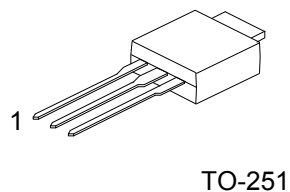
NPN SILICON TRANSISTOR

NPN POWER TRANSISTORS

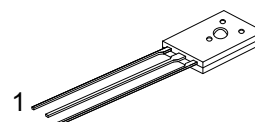
■ FEATURES

* High current (max.1.5A)

* Low voltage (max.80V)



TO-251



TO-126

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BD139L-xx-T60-K	BD139G-xx-T60-K	TO-126	E	C	B	Bulk
BD139L-xx-TM3-T	BD139G-xx-TM3-T	TO-251	B	C	E	Tube

BD139L-xx-T60-K	(1)Packing Type	(1) K: Bulk, T: Tube
	(2)Package Type	(2) T60: TO-126, TM3: TO-251
	(3)Rank	(3) refer to h_{FE}
	(4)Lead Plating	(4) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATING

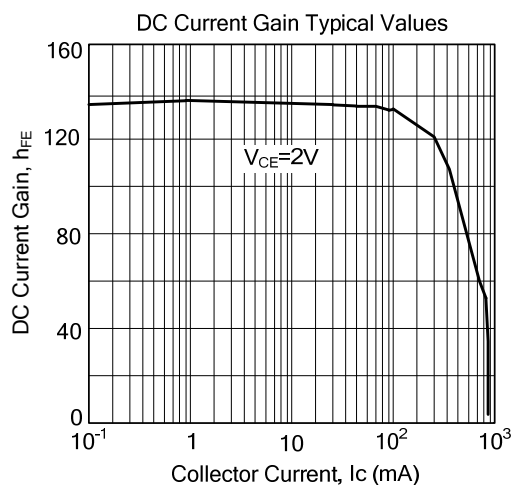
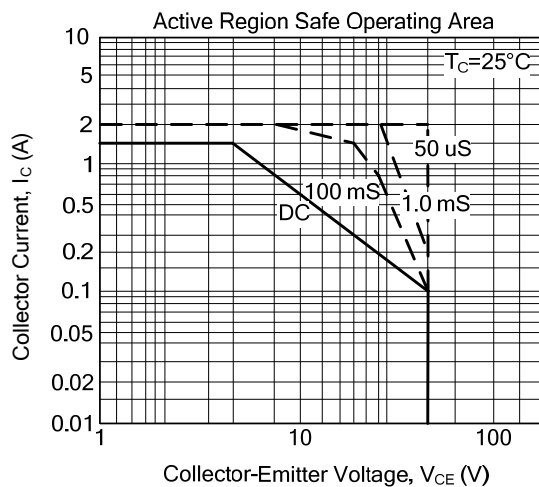
PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	100	V
Collector-Emitter Voltage		V_{CEO}	80	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current (DC)		I_C	1.5	A
Peak Collector Current		I_{CM}	2	A
Peak Base Current		I_{BM}	1	A
Power Dissipation ($T_a=25^\circ\text{C}$)	TO-126	P_D	1.25	W
	TO-251		1	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-65~+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-65~+150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current		I_{CBO}	$I_E=0, V_{CB}=30\text{V}$			100	nA
			$I_E=0, V_{CB}=30\text{V}, T_J=125^\circ\text{C}$			10	μA
Emitter Cut-Off Current		I_{EBO}	$I_C=0, V_{EB}=5\text{V}$			100	nA
DC Current Gain		h_{FE}	$V_{CE}=2\text{V}$ (See Fig.1)	$I_C=5\text{mA}$	40		
				$I_C=150\text{mA}$	63	250	
				$I_C=500\text{mA}$	25		
DC Current Gain	BD139-10		$I_C=150\text{mA}, V_{CE}=2\text{V}$ (See Fig.1)		63	160	
	BD139-16				100	250	
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.5	V
Base-Emitter Voltage		V_{BE}	$I_C=500\text{mA}, V_{CE}=2\text{V}$			1	V
Transition Frequency		f_T	$I_C=500\text{mA}, V_{CE}=5\text{V}, f=100\text{MHz}$		190		MHz

TYPICAL CHARACTERISTICS



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